

NTE1722 Integrated Circuit Pulse Width Modulator (PWM) Control Circuit

Description:

The NTE1722 is a high performance pulse width modulator integrated circuit in an 18-Lead DIP type package intended for fixed frequency switching regulators and other power control applications.

Functions included in this IC are a temperature compensated voltage reference, sawtooth oscillator, error amplifier, pulse width modulator, pulse metering and steering logic, and two high current totem pole outputs ideally suited for driving the capacitance of power FETs at high speeds.

Additional protective features include soft start and undervoltage lockout, digital current limiting, double pulse inhibit, adjustable dead time and a data latch for single pulse metering. All digital control ports are TTL and B-series CMOS compatible. Active low logic design allows easy wired-OR connections for maximum flexibility. The versatility of this device enables implementation in single-ended or push-pull switching regulators that are transformerless or transformer coupled.

Features:

- 8.0 to 35 Volt Operation
- 5.0 Volt $\pm 1\%$ Trimmed Reference
- 1.0Hz to 400kHz Oscillator Range
- Dual Source/Sink Current Outputs: $\pm 100\text{mA}$
- Digital Current Limiting
- Programmable Dead Time
- Wide Current Limit Common Mode Range
- Guaranteed 6 Unit Synchronization

Absolute Maximum Ratings: (Values beyond which damage may occur)

Supply Voltage, V_{CC}	+40V
Collector Supply Voltage, V_C	+40V
Logic Inputs	-0.3 to +5.5V
Analog Inputs	-0.3 to V_{CC} V
Output Current (Source or Sink), I_O	$\pm 200\text{mA}$
Reference Load Current ($V_{CC} = 40\text{V}$, Note 1), I_{ref}	50mA
Logic Sink Current	15mA
Power Dissipation ($T_A = +25^\circ\text{C}$), P_D	1000mW
Derate Above 50°C	10mW/ $^\circ\text{C}$
Power Dissipation ($T_C = +25^\circ\text{C}$), P_D	3000mW
Derate Above 25°C	24mW/ $^\circ\text{C}$
Operating Junction Temperature, T_J	+ 150°C
Storage Temperature Range, T_{stg}	-65° to $+150^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient, R_{thJA}	100 $^\circ\text{C/W}$
Lead Temperature (During Soldering, 10sec), T_L	$\pm 300^\circ\text{C}$

Note 1. Maximum junction temperature must be observed.

Recommended Operating Conditions:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Supply Voltage	V_{CC}		+8.0	–	+35	V
Collector Supply Voltage	V_C		+4.5	–	+35	V
Output Sink/Source Current (Each Output)	I_O		0	–	± 100	mA
Reference Load Current	I_{ref}		0	–	20	mA
Oscillator Frequency Range	I_{ref}		0	–	20	mA
Oscillator Timing Resistor	R_T		2.0	–	150	k Ω
Oscillator Timing Capacitor	C_T		0.001	–	20	μ F
Available Deadtime Range (40kHz)	–		3.0	–	50	%
Operating Junction Temperature Range	T_J		0	–	+125	$^{\circ}$ C

Electrical Characteristics: ($V_{CC} = 15V$, $T_J = 0^{\circ}$ to $+125^{\circ}$ C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Referend Section (I _L = 0mA unless otherwise specified)						
Reference Output Voltage	V _{ref}	T _J = +25°C	4.90	5.00	5.10	V
Line Regulation	Reg _{line}	+8.0V ≤ V _{CC} ≤ +35V	–	10	30	mV
Load Regulation	Reg _{load}	0mA ≤ I _L ≤ 20mA	–	10	50	mV
Temperature Stability	ΔV _{ref} /ΔT _J		–	10	–	mV
Total Reference Output Voltage Variation	ΔV _{ref}	+8.0V ≤ V _{CC} ≤ +35V, 0mA ≤ I _L ≤ 20mA	4.85	5.00	5.15	V
Short Circuit Current	I _{SC}	V _{ref} = 0V, Note 1	25	80	125	mA
Undervoltage Lockout						
Reset Output Voltage	–	V _{ref} = +3.8V	–	0.2	0.4	V
		V _{ref} = +4.8V	2.4	4.8	–	V
Oscillator Section (Note 2)						
Initial Accuracy	–	T _J = +25°C	–	±3.0	±8.0	%
Frequency Stability over Power Supply Range	$\frac{\Delta f_{osc}}{\Delta V_{CC}}$	+8.0V ≤ V _{CC} ≤ +35V	–	0.5	1.0	%
Frequency Stability over Temperature	$\frac{\Delta f_{osc}}{\Delta T_J}$	ΔT _J = 0° to +125°C	–	2.0	–	%
Minimum Frequency	f _{min}	R _T = 150kΩ, C _T = 20μF	–	0.5	–	Hz
Maximum Frequency	f _{max}	R _T = 2kΩ, C _T = 0.001μF	400	–	–	kHz
Sawtooth Peak Voltage	V _{osc(p)}	V _{CC} = +35V	–	3.0	3.5	V
Sawtooth Valley Voltage	V _{osc(v)}	V _{CC} = +8V	0.45	0.8	–	V
Error Amplifier Section (0V ≤ V _{CM} ≤ +5.2V unless otherwise specified)						
Input Offset Voltage	V _{IO}	R _S ≤ 2kΩ	–	20	10	mV
Input Bias Current	I _{IB}		–	–350	–2000	nA
Input Offset Current	I _{IO}		–	35	200	nA
DC Open Loop Gain	A _{VOL}	R _L ≥ 10MΩ	60	72	–	dB

Note 1. Maximum junction temperature must be observed.

Note 2. $f_{OSC} = 40kHz$ ($R_T = 4.12k\Omega \pm 1\%$, $C_T = 0.01\mu F \pm 1\%$, $R_D = 0\Omega$)

Electrical Characteristics (Cont'd): ($V_{CC} = 15V$, $T_J = 0^\circ$ to $+125^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Error Amplifier Section (Cont'd) ($0V \leq V_{CM} \leq +5.2V$ unless otherwise specified)						
High Output Voltage	V_{OH}	$V_{Pin1} - V_{Pin2} \geq +150mV$, $I_{Source} = 100\mu A$	3.6	4.2	–	V
Low Output Voltage	V_{OL}	$V_{Pin2} - V_{Pin1} \geq +150mV$, $I_{Sink} = 100\mu A$	–	0.2	0.4	V
Common Mode Rejection Ratio	CMRR	$R_S \leq 2k\Omega$	70	94	–	dB
Power Supply Rejection Ratio	PSRR	$+12V \leq V_{CC} \leq +18V$	66	80	–	dB
PWM Comparator Section (Note 2)						
Minimum Duty Cycle	DC_{min}	$V_{compensation} = +0.4V$	–	–	0	%
Maximum Duty Cycle	DC_{max}	$V_{compensation} = +3.6V$	45	49	–	%
Digital Ports (SYNC, SHUTDOWN, RESET)						
Output Voltage, High Logic Level	V_{OH}	$I_{source} = 40\mu A$	2.4	4.0	–	V
Output Voltage, Low Logic Level	V_{OL}	$I_{sink} = 3.6mA$	–	0.2	0.4	V
Input Current, High Logic Level	I_{IH}	$V_{IH} = +2.4V$	–	–125	–200	μA
Input Current, Low Logic Level	I_{IL}	$V_{IL} = +0.4V$	–	–225	–360	μA
Current Limit Comparator Section ($0V \leq V_{CM} \leq +12V$ unless otherwise specified)						
Sense Voltage	V_{sense}	$R_S \leq 50\Omega$	80	100	120	mV
Input Bias Current	I_{IB}		–	–3	–10	μA
Soft-Start Section						
Error Clamp Voltage		$Reset = +0.4V$	–	0.1	0.4	V
$C_{Soft-Start}$ Charging Current	I_{CS}	$Reset = +2.4V$	50	100	150	μA
Output Drivers (Each Output, $V_C = +15Vdc$ unless otherwise specified)						
Output High Level	V_{OH}	$I_{source} = 20mA$	12.5	13.5	–	V
		$I_{source} = 100mA$	12.0	13.0	–	V
Output Low Level	V_{OL}	$I_{Sink} = 20mA$	–	0.2	0.3	V
		$I_{Sink} = 100mA$	–	1.2	2.0	V
Collector Leakage	$I_{C(Leak)}$	$V_C = +40V$	–	50	150	μA
Rise Time	t_r	$C_L = 1000pF$	–	0.3	0.6	μs
Fall Time	t_f		–	0.1	0.2	μs
Supply Current	I_{CC}	Shutdown + $+0.4V$, $V_{CC} = +35V$, $R_T = 4.12k\Omega$	–	18	30	mA

Note 2. $f_{OSC} = 40kHz$ ($R_T = 4.12k\Omega \pm 1\%$, $C_T = 0.01\mu F \pm 1\%$, $R_D = 0\Omega$)

Pin Connection Diagram

